Rb₂Cu₃CeTe₅: a quaternary semiconducting compound with a two-dimensional polytelluride framework

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Rb₂Cu₃CeTe₅ has been synthesized from the reaction of Cu and Ce in a molten alkali metal/polytelluride flux. The compound crystallizes in the monoclinic space group, C2/m (no. 12) with a=18.6884(1) Å, b=6.2384(2) Å, c=12.5264(3) Å, $\beta=112.795(1)^{\circ}$, V=1346.34(5) Å³, and Z=4. Rb₂Cu₃CeTe₅ is two-dimensional with $\frac{1}{\infty}$ [Cu₃CeTe₅]²⁻ layers built from one-dimensional $\frac{1}{\infty}$ [Cu₂CeTe₅]³⁻ chains that are 'stitched' together by distorted tetrahedral Cu atoms; the compound is paramagnetic and a narrow-gap p-type semiconductor.

Over the past decade, the polychalcogenide flux method has become an established technique for discovering new solid state chalcogenides.¹ Although many of the compounds form completely new structure types, others are reminiscent of, or can be considered derivatives of known chalcogenides. This is particularly true when lanthanide and actinide metals are involved. The binary LnQ₃ phases (NdTe₃² and ZrSe₃³ type), for example, are quite stable. Several new ternary phases have recently been reported in which the structural motifs are related to these LnQ_3 binaries. While $NaLnS_3$ (Ln = La, Ce)⁴ and ATh_2Q_6 (A = Cs, Rb, K; Q = Se, Te)⁵ represent two different variations of the $ZrSe_3$ structure type, ALn_3Te_8 (A = Cs, Rb, K; $Ln = Ce, Nd)^6$ is closely related to the structure of NdTe₃. In an effort to access quaternary phases which are less structurally related to the LnQ₃ binaries, another element was introduced into the synthesis. Copper proved to be well behaved in this respect and we were able to isolate several compounds, whereas other elements gave phase-separated ternary compounds. Reactions in the A/Cu/Ln/Q (Q = S,Se) system have produced several quaternary compounds, including K₂Cu₂CeS₄,⁷ KCuCe₂S₆,^{7,8} KCuLa₂S₆,⁸ CsCuCe₂S₆,⁸ CsCuCeS₃⁸ and KCuUSe₃.⁸ Other investigators have identified such compounds as BaErAgS₃,⁹ CsCuUTe₃,¹⁰ BaLnMQ₃ (Ln = La,Ce,Nd; M = Cu,Ag; Q = S,Se)¹¹ and KCuEu₂S₆.¹² Although many of these phases are structurally unique, some still retain the components of the LnQ₃ motif. It is apparent that the greater the amount of copper in the framework, the more profound the effect of breaking up the LnQ₃ structure. Along these lines, we examined the A/M/Ln/Te (M=Cu,Ag) system using polytelluride fluxes and discovered several novel compounds including KCuCeTe₄,¹³ K₂Ag₃CeTe₄¹⁴ and K_{2.5}Ag_{4.5}Ce₂Te₉.¹⁵ We report here on Rb₂Cu₃CeTe₅,¹⁶ a lowdimensional compound in which the basic LnQ₃ structure is substantially disrupted.

 $Rb_2Cu_3CeTe_5$ consists of $\frac{1}{\infty}[Cu_3CeTe_5]^{2^-}$ layers separated by Rb^+ cations (Fig. 1.) The Ce atom is seven coordinate, exhibiting a distorted pentagonal bipyramidal geometry in which one η^2 -(Te₂²⁻) unit¹⁷ and three Te²⁻ anions comprise the pentagon and two Te²⁻ anions occupy the axial positions [Fig. 2(A)]. The pentagonal bipyramids share monotelluride ions, forming $\frac{1}{\infty}$ [CeTe₅]⁵⁻ chains parallel to the *b*-axis.

Fig. 1 ORTEP representation of the structure of $Rb_2Cu_3CeTe_5$ as seen down the *b*-axis (90% ellipsoids). The ellipses with octant shading represent Ce and Rb, the crossed ellipses represent Cu and the open ellipses represent Te.

Conceptually, these one-dimensional chains derive from the $ZrSe_3$ structure type. By replacing one $(Q_2^{2^-})$ unit in the $ZrSe_3$ framework with a Q^{2-} unit, the coordination environment of the metal changes from bicapped trigonal prismatic to pentagonal bipyramidal. This change in coordination is accompanied by a conversion from two-dimensional layers to one-dimensional chains. Within the $\frac{1}{\infty}$ [CeTe₅]⁵⁻ chains exist empty distorted tetrahedral pockets of Te atoms which are large enough to accommodate Cu atoms. Each Cu atom is bonded at two points to the axial positions of two neighboring pentagonal bipyramids, and at the remaining sites to the closest edge between these axial positions. The chains, once extended to include the Cu atom, can be written as $\frac{1}{m}$ $[Cu_2CeTe_5]^{3-}$. Finally, the layers are formed when the second type of Cu atom 'stitches' these chains together in the adirection by coordinating to neighboring chains in a distorted tetrahedral arrangement. A view perpendicular to the layers is shown in Fig. 2(B). It is interesting that if one removes the Ce atoms from the structure, the remaining [Cu₃Te₃] substructure remains contiguous. In this sense, the Ce atoms are situated on both sides of a two-dimensional [CuTe]⁻ substrate. In fact, this copper telluride framework, albeit distorted, bears a close resemblance to the layers of NaCuTe¹⁸ [Fig. 2(C)].

The magnetic susceptibility of $Rb_2Cu_3CeTe_5$ was measured over the range 5–300K at 6000 G, and a plot of $1/\chi_m$ vs. T shows that the material exhibits nearly Curie–Weiss behavior with only slight deviation from linearity beginning below 50 K. Such deviation has been reported for several Ce^{3+} compounds and has been attributed to crystal field splitting of the ${}^3F_{5/2}$ ground state of the cation.¹⁹ At temperatures above 150 K,





Fig. 2 (A) Schematic comparison of the two-dimensional layers of ZrSe₃, the one-dimensional $\frac{1}{\infty}$ [CeTe₅]⁵⁻ chains and the $\frac{1}{\infty}$ [Cu₂CeTe₅]³⁻ chains in Rb₂Cu₃CeTe₅. The dotted line highlights the pentagonal bipyramidal coordination around Ce. Selected distances (Å) are as follows: Ce–Te1 3.161(1), Ce–Te2 3.2538(5), Ce–Te3 3.246(2), Ce–Te4 3.253(2) and Te1–Te1 2.771(2). (B) View perpendicular to the layers of Rb₂Cu₃CeTe₅, illustrating how the second Cu atom stitches together the $\frac{1}{\infty}$ [Cu₂CeTe₅]³⁻ chains to form two-dimensional layers. The ditelluride groups above and below the anionic layers are omitted for clarity. Selected distances (Å): Cu1–Te2 2.820(2), Cu1–Te3 2.591(2), Cu1–Te4 2.593(2), Cu1–Ce1 3.332(2), Cu1–Cu2 2.650(2), Cu2–Te3 2.721(2), Cu2–Te4 2.721(2) and 2.593(2). (C) The distorted [CuTe]⁻, PbO-like layer in Rb₂Cu₃CeTe₅.

a μ_{eff} of 2.64 μ_B has been calculated, which is in accord with the usual range for Ce³⁺ compounds (2.3–2.5 μ_B). The presence of Ce³⁺ is confirmed by IR spectroscopy with shows one well defined, broad peak at *ca.* 3420 cm⁻¹ (0.42 eV) This absorption is electronic in origin and is attributed to an f–f or f–d transition within the f¹ configuration of Ce³⁺. From this we can conclude that Rb₂Cu₃CeTe₅ is a valence precise compound, and thus we expect semiconducting properties. The formal oxidation states are $(Rb^{1+})_2(Cu^{1+})_3(Ce^{3+})$ - $(Te^{2-})_3(Te_2^{2-})$.

The electrical conductivity of $Rb_2Cu_3CeTe_5$ as a function of temperature measured on single crystals suggests that the material is indeed a narrow gap semiconductor with a room temperature conductivity value of 0.05 S cm⁻¹ [Fig. 3(A)]. The log σ vs. 1/T plot is non-linear over the entire temperature range of 8–300 K, suggesting the conduction mechanism varies in different temperature regions, possibly due to different types of mid-gap states. Thermoelectric power data as a function of temperature show a large Seebeck coefficient at room temperature of +275 μ V K⁻¹ [Fig. 3(B)]. The increasing Seebeck coefficient with decreasing temperature and its positive sign are consistent with a p-type semiconductor.

Note added in proof. By the time we received proofs of this manuscript we became aware of the syntheses of BaDyCuTe₃, $K_{1.5}Dy_2Cu_{2.5}Te_5$ and $K_{0.5}Ba_{0.5}DyCu_{1.5}Te_3$ (F. Q. Huang, W. Choe, S. Lee and J. S. Chu, *Chem. Mater.*, 1998, **10**, 1320). These compounds are not structurally related to the one reported here; however, they do belong in the broad quaternary family of A/Cu/Ln/Q compounds.

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Fig. 3 (A) Variable temperature, four-probe electrical conductivity data for a single crystal of $Rb_2Cu_3CeTe_5$. (B) Variable temperature thermopower data for a single crystal of $Rb_2Cu_3CeTe_5$.

crystal X-ray data set. M.G.K. is a Henry Dreyfus Teacher Scholar 1993–1998. This work made use of the SEM facilities of the center for Electron Optics at Michigan State University. At Northwestern University, this work made use of the Central Facilities supported by NSF through the Materials Research Center (DMR-9632472).

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- 16 (a) Rb₂Cu₃CeTe₅ was synthesized from a mixture of 0.448 g Rb₂Te (3.0 mmol), 0.095 g Cu (3.0 mmol), 0.070 g Ce (1.0 mmol) and

0.447 g Te (7.0 mmol) which was sealed under vacuum in a carbon coated quartz tube and heated to 850 °C for 10 days. The tube was then cooled to 400 °C at -3 °C h⁻¹, and then quenched to room temperature. The excess Rb_xTe_y flux was removed, under nitrogen atmosphere, with dimethylformamide to reveal black needle-shaped crystals in 45% yield (based on Cu). The crystals are air and water stable. Phase homogeneity was confirmed by comparing the power X-ray diffraction pattern of the product against that calculated using the crystallographically determined atomic coordinates. Microprobe analysis carried out on randomly selected crystals gave an average composition of Rb_{2.46}Cu_{3.29}Ce_{1.0}Te_{5.55}. A Siemens SMART Platform CCD diffractometer was used to collect data from a crystal of 0.160 × 0.035 × 0.010 mm dimensions using Mo-K α (λ =0.71073 Å) radiation. SMART^{16b} software was used for data acquisition and SAINT^{16c} for data extraction and reduction. An absorption correction was performed using SADABS.^{16d}

Crystal data at 173 K: a=18.6884(1), b=6.2384(2), c=12.5264(3) Å, $\beta=112.795(1)^\circ$, V=1346.34(5) Å³, Z=4, $D_c=5.623$ g cm⁻³, monoclinic, space group C2/m (no. 12), $\mu=25.741$ mm⁻¹, index ranges $-22 \le h \le 20$, $0 \le k \le 7$, $0 \le l \le 14$, $2\theta_{max}=50^\circ$, total data 3427, unique data 1307 ($R_{int}=0.044$), data with $F_o^2 > 2\sigma(F_o^2)$ 1087, no. of variables 60, final R/wR2=0.0461/0.1182, GOF 1.041. The structure was solved and refined using the SHELXTL-5 package of crystallographic programs;^{16e} SHELXTL refines on F^2 . (*b*) SMART: 1994, Siemens Analytical Xray Systems, Inc., Madison, WI 53719 USA; (*c*) SAINT: Version 4, 1994–1996, Siemens Analytical Xray Systems, Inc., Madison, WI 53719 USA; (*d*) SADABS: G.M. Sheldrick, University of Göttingen, Germany, to be published. (*e*) SHELXTL: Version 5, 1994, G.M. Sheldrick, Siemens Analytical X-ray Instruments, Inc. Madison, WI 53719. Full crystallographic details, excluding structure factors, have been deposited at the Cambridge Crystallographic Data Centre (CCDC). Any request to the CCDC for this material should quote the full literature citation and the reference number 1145/124.

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